

REPLACEMENT PARAGRAPHS

Replace the paragraph beginning on page 6, line 17 with:

Shown in FIG. 9 is SOI device 60 comprising a substrate 62 having a contact region 63 formed therein. SOI device 10 further comprises an insulator layer 64, an active layer 66, and an isolation region 68. Isolation region 68 is adjacent to active layer 66 and both overlie insulator layer 64. Contact region 63 is formed by a blanket implant of preferably boron at 100 KeV. The boron is preferred over indium because it is lighter. Indium may be effective as well, but boron will more easily penetrate through active layer 66 and isolation region 68 as well as insulator layer 64. Thus, the result of the implant of boron is a heavily doped contact region which is under insulator layer 64 throughout a particular semiconductor wafer. SOI device 60 shows only a portion of a complete die and wafer. The structure shown in FIG. 9 is conventional except for the implant and the consequent effect of the implant. The formation of an isolation region 68 adjacent to an active layer 66 overlying an insulator 64 which in turn overlies a substrate of silicon is conventional. The implant at this point provides for the beneficial contact region 63 which is not conventional.

